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### Vishay Semiconductors

## Insulated Gen 2 Schottky Rectifier Module, 300 A



SOT-227

### **ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS						
$I_{F(AV)}$ per module at $T_C = 132  ^{\circ}C$	300 A					
$V_R$	170 V					
$V_{FM}$ at 100 A, $T_C = 25$ °C	0.79 V					
Package	SOT-227					
Circuit configuration	Two separate diodes, parallel pin-out					

#### **FEATURES**

- Max. T<sub>J</sub> = 175 °C
- Two fully independent diodes
- Fully insulated package
- Trench MOS Barrier Schottky technology
- Ultra low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- Industry standard outline
- Designed and qualified for industrial level
- UL approved file E78996



 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **DESCRIPTION**

The VS-QA300FA17 insulated modules integrate two state of the art Trench MOS Schottky technology rectifiers in the compact, industry standard SOT-227 package.

These devices are thus intended for high frequency converters and switching power supplies.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL CHARACTERISTICS VALUES UNITS					
V <sub>F</sub>	T <sub>J</sub> = 150 °C	0.69	V		
T <sub>J</sub>	Range	-55 to +175	°C		

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Average forward current per module	I <sub>F(AV)</sub>	T <sub>C</sub> = 132 °C	300	Α	
Cathode to anode voltage	$V_R$		170	V	
Continuous forward current per diode	I <sub>F</sub>	T <sub>C</sub> = 90 °C	330	۸	
Single pulse forward current per diode	I <sub>FSM</sub>	$T_C = 175$ °C, t = 6 ms, square	1575	А	
Maximum power dissipation per diode	$P_D$	T <sub>C</sub> = 90 °C	327	W	
Non-repetitive avalanche energy per diode	E <sub>AS</sub>	$T_J = 25  ^{\circ}\text{C},  I_{AS} = 27  \text{A},  L = 10  \text{mH}$	3700	mJ	
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 min	2500	V	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	



<b>ELECTRICAL SPECIFICATIONS PER DIODE</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	MBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 2 mA	170	-	-	
		I <sub>F</sub> = 100 A	-	0.79	0.85	
Forward voltage V <sub>FM</sub>	\ \	I <sub>F</sub> = 100 A, T <sub>J</sub> = 150 °C	=	0.62	=	V
	I <sub>F</sub> = 200 A	-	0.89	0.98		
		I <sub>F</sub> = 200 A, T <sub>J</sub> = 150 °C	=	0.75	=	
Reverse leakage current I <sub>RM</sub>	V <sub>R</sub> = 170 V	=	13	200	μΑ	
	T <sub>J</sub> = 125 °C, V <sub>R</sub> = 170 V	-	20	-	mA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 170 V	-	737	-	pF

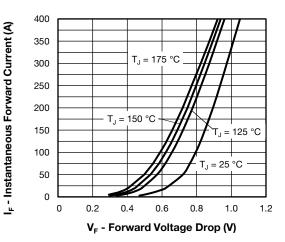
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Deverse receiver time		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 50 A	-	71	-	ns
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		=	82	-	
Peak recovery current I <sub>RRM</sub>		T <sub>J</sub> = 25 °C		-	7.1	-	^
	T <sub>J</sub> = 125 °C	$di_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 100 \text{ V}$	=	8.8	-	Α	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	, , , , , , , , , , , , , , , , , , ,	-	252	-	nC
		T <sub>J</sub> = 125 °C		-	352	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction-to-case, single leg conducting			-	-	0.26	
Junction-to-case, both leg conducting	$R_{thJC}$		-	-	0.13	°C/W
Case-to-heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				SC	T-227	



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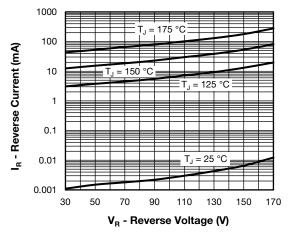


Fig. 1 - Typical Forward Voltage Drop vs. Instantaneous Forward Current (Per Diode)

Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Diode)

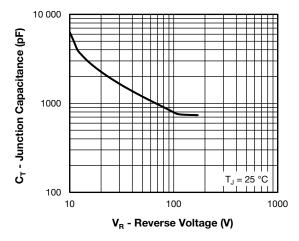


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Diode)

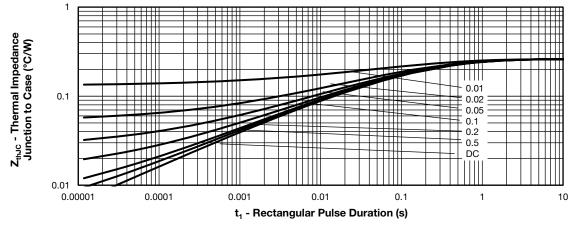


Fig. 4 - Maximum Thermal Impedance Junction-to-Case Characteristics (Per Diode)



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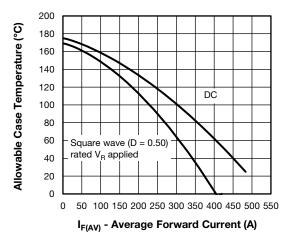


Fig. 5 - Maximum Current Rating Capability (Per Diode)

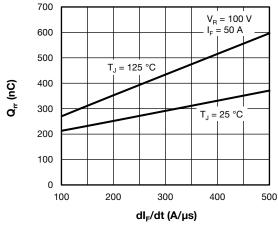


Fig. 7 - Typical Reverse Recovery Charge vs dl<sub>F</sub>/dt (Per Diode)

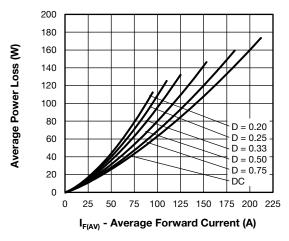


Fig. 6 - Forward Power Loss Characteristics (Per Diode)

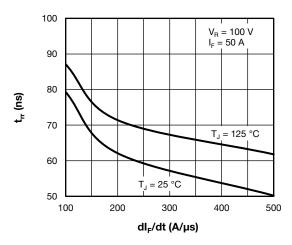


Fig. 8 - Typical Reverse Recovery Time vs dl<sub>F</sub>/dt (Per Diode)

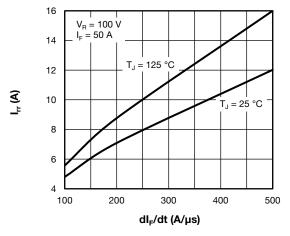


Fig. 9 - Typical Reverse Recovery Current vs dIFdt (Per Diode)

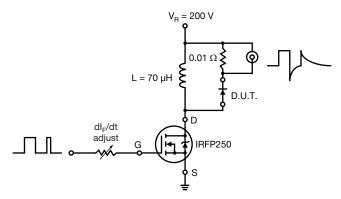
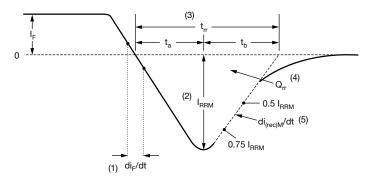


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

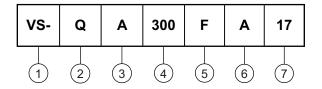
(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 11 - Reverse Recovery Waveform and Definitions



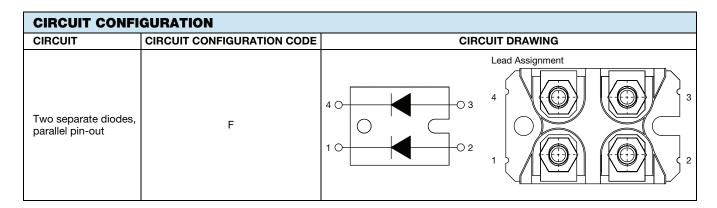
### **ORDERING INFORMATION TABLE**

Device code



- 1 Vishay Semiconductors product
- 2 Schottky technologies
- Present silicon generation
- **4** Current rating (300 = 300 A)
- 5 Circuit configuration (two separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (17 = 170 V)

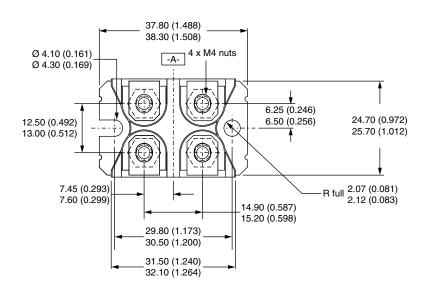
Quantity per tube is 10, M4 screw and washer included

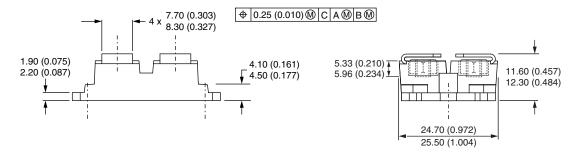


LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95423</u>					
Part marking information	www.vishay.com/doc?95425				

### SOT-227 Generation 2

### **DIMENSIONS** in millimeters (inches)





### Note

· Controlling dimension: millimeter



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